



JIANGSU CHANGJIANG ELECTRONICS TECHNOLOGY CO., LTD

## WBFBP-06C Power management Dual-transistors

### FUMF21N TRANSISTOR

#### DESCRIPTION

Silicon epitaxial planar transistor

#### FEATURES

- 2SA2018 and DTC114E are housed independently in a package.
- Power switching circuit in a single package.
- Mounting cost and area can be cut in half.

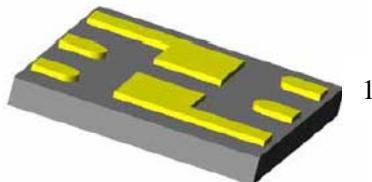
#### APPLICATION

Power management circuit, mobile telephone quiver circuit  
For portable equipment:(i.e. Mobile phone,MP3, MD,CD-ROM,  
DVD-ROM, Note book PC, etc.)

#### WBFBP-06C

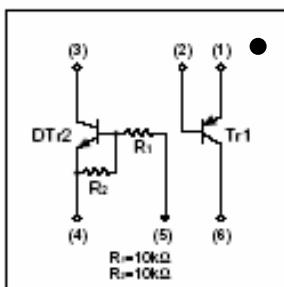
(2×2×0.5)

unit: mm



1

#### ●Equivalent circuits



#### MARKING:F21



TR1 MAXIMUM RATINGS  $T_A=25^\circ\text{C}$  unless otherwise noted

Symbol	Parameter	Value	Units
$V_{CBO}$	Collector- Base Voltage	-15	V
$V_{CEO}$	Collector-Emitter Voltage	-12	V
$V_{EBO}$	Emitter-Base Voltage	-6	V
$I_C$	Collector Current -Continuous	-0.5	A
$P_c$	Collector Dissipation	0.15	W
$T_J$	Junction Temperature	150	$^\circ\text{C}$
$T_{stg}$	Storage Temperature	-55-150	$^\circ\text{C}$

#### DTR2 Absolute maximum ratings( $T_a=25^\circ\text{C}$ )

Parameter	Symbol	Limits	Unit
Supply voltage	$V_{CC}$	50	V
Input voltage	$V_{IN}$	-10~40	V
Output current	$I_O$	50	mA
	$I_{C(MAX)}$	100	
Power dissipation	$P_d$	150	mW
Junction temperature	$T_j$	150	$^\circ\text{C}$
Storage temperature	$T_{stg}$	-55~150	$^\circ\text{C}$

**TR1 ELECTRICAL CHARACTERISTICS (T<sub>amb</sub>=25°C unless otherwise specified)**

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
<b>Collector-base breakdown voltage</b>	V <sub>(BR)CBO</sub>	I <sub>C</sub> =-10µA, I <sub>E</sub> =0	-15			V
<b>Collector-emitter breakdown voltage</b>	V <sub>(BR)CEO</sub>	I <sub>C</sub> =-1mA, I <sub>B</sub> =0	-12			V
<b>Emitter-base breakdown voltage</b>	V <sub>(BR)EBO</sub>	I <sub>E</sub> =-10µA, I <sub>C</sub> =0	-6			V
<b>Collector cut-off current</b>	I <sub>CBO</sub>	V <sub>CB</sub> = -15 V, I <sub>E</sub> =0			-0.1	µA
<b>Emitter cut-off current</b>	I <sub>EBO</sub>	V <sub>EB</sub> =- 6V, I <sub>C</sub> =0			-0.1	µA
<b>DC current gain</b>	h <sub>FE</sub>	V <sub>CE</sub> =-2V, I <sub>C</sub> =-10mA	270		680	
<b>Collector-emitter saturation voltage</b>	V <sub>CE(sat)</sub>	I <sub>C</sub> =-200mA,I <sub>B</sub> =-10mA			-0.25	V
<b>Transition frequency</b>	f <sub>T</sub>	V <sub>CE</sub> =-2V,I <sub>C</sub> =-10mA, f=100MHz		260		MHz
<b>Collector output capacitance</b>	C <sub>ob</sub>	V <sub>CB</sub> =-10V,I <sub>E</sub> =0,f=1MHz		6.5		pF

**DTR2 Electrical characteristics (Ta=25°C)**

Parameter	Symbol	Min.	Typ	Max.	Unit	Conditions
<b>Input voltage</b>	V <sub>I(off)</sub>			0.5	V	V <sub>CC</sub> =5V ,I <sub>O</sub> =100µA
	V <sub>I(on)</sub>	3				V <sub>O</sub> =0.3V ,I <sub>O</sub> =10 mA
<b>Output voltage</b>	V <sub>O(on)</sub>			0.3	V	I <sub>O</sub> /I <sub>i</sub> =10mA/0.5mA
<b>Input current</b>	I <sub>i</sub>			0.88	mA	V <sub>i</sub> =5V
<b>Output current</b>	I <sub>O(off)</sub>			0.5	µA	V <sub>CC</sub> =50V, V <sub>i</sub> =0
<b>DC current gain</b>	G <sub>i</sub>	30				V <sub>O</sub> =5V ,I <sub>O</sub> =5mA
<b>Input resistance</b>	R <sub>1</sub>	7	10	13	KΩ	
<b>Resistance ratio</b>	R <sub>2</sub> /R <sub>1</sub>	0.8	1	1.2		
<b>Transition frequency</b>	f <sub>T</sub>		250		MHz	V <sub>CE</sub> =10V ,I <sub>E</sub> =-5mA,f=100MHz

# Typical Characteristics

TR1

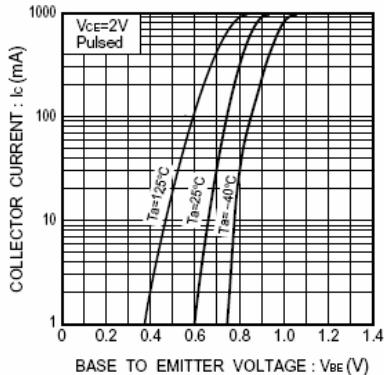


Fig.1 Grounded emitter propagation characteristics

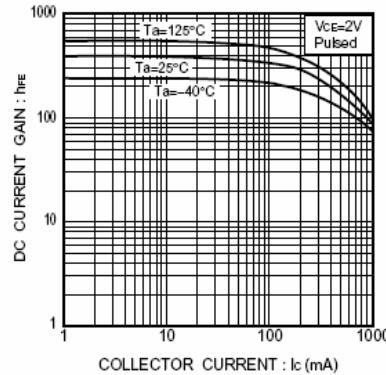


Fig.2 DC current gain vs. collector current

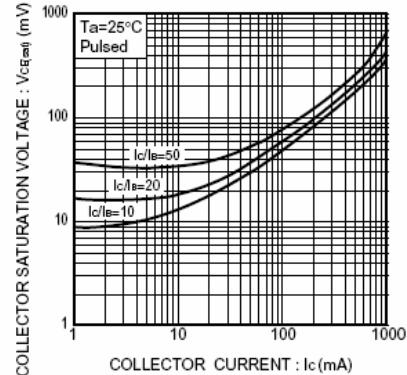


Fig.3 Collector-emitter saturation voltage vs. collector current ( I )

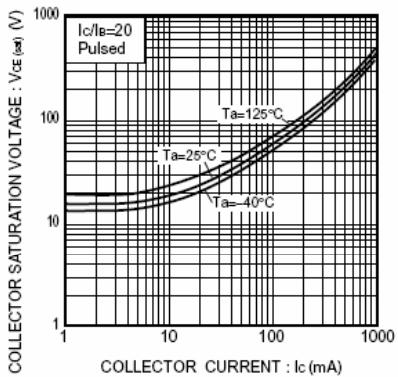


Fig.4 Collector-emitter saturation voltage vs. collector current ( II )

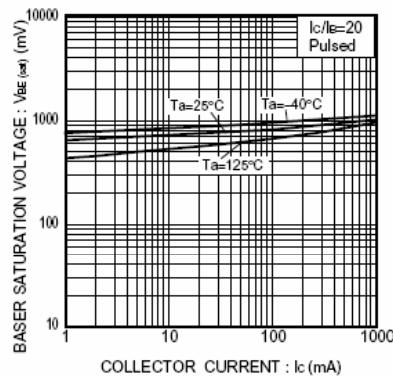


Fig.5 Base-emitter saturation voltage vs. collector current

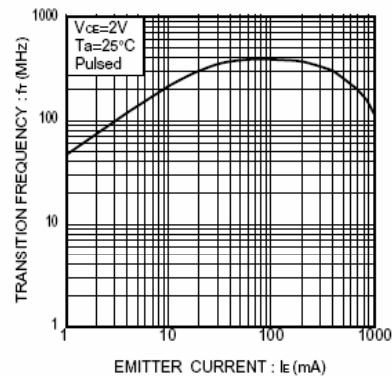


Fig.6 Gain bandwidth product vs. emitter current

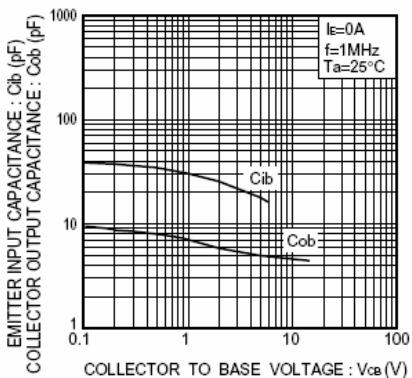


Fig.7 Collector output capacitance vs. collector-base voltage  
Emitter input capacitance vs. emitter-base voltage

## DTR2

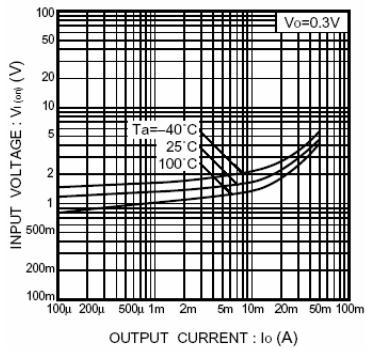


Fig.1 Input voltage vs. output current  
(ON characteristics)

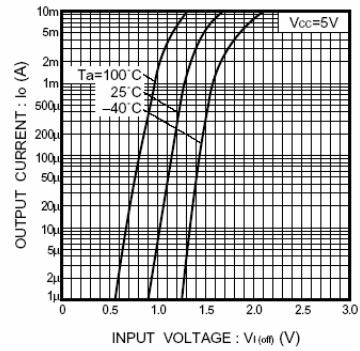


Fig.2 Output current vs. input voltage  
(OFF characteristics)

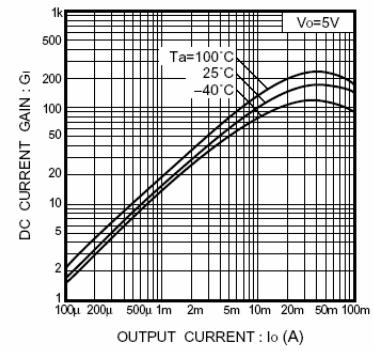


Fig.3 DC current gain vs. output current

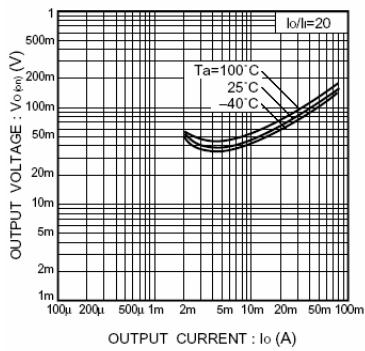
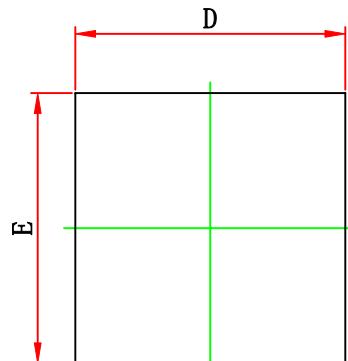


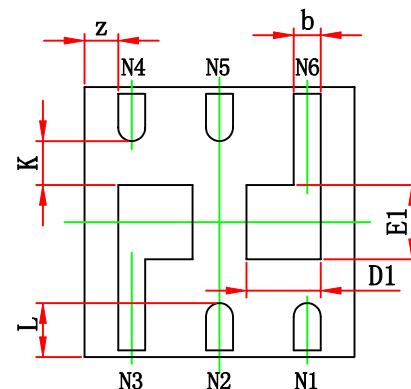
Fig.4 Output voltage vs. output current



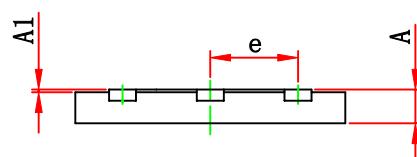
### WBFBP-06C(2×2×0.5) PACKAGE OUTLINE DIMENSIONS



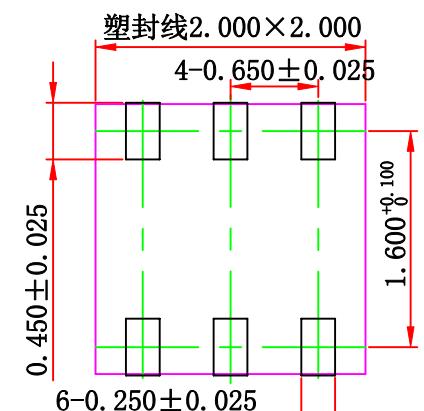
TOP VIEW



BOTTOM VIEW



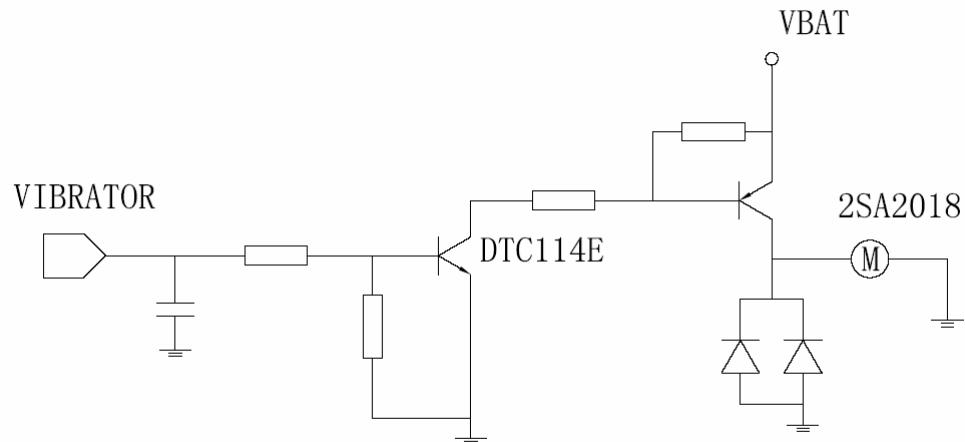
SIDE VIEW



LAND PATTERN RECOMMENDATION  
推荐焊盘图

Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	0.450	0.550	0.018	0.022
A1	0.000	0.100	0.000	0.004
b	0.150	0.250	0.006	0.010
D	1.900	2.100	0.075	0.083
E	1.900	2.100	0.075	0.083
D1	0.550 REF.		0.022 REF.	
E1	0.550 REF.		0.022 REF.	
e	0.650 TYP.		0.026 TYP.	
L	0.400 REF.		0.016 REF.	
k	0.300 REF.		0.012 REF.	
z	0.500 REF.		0.020 REF.	

## APPLICATION CIRCUITS



mobile telephone quiver circuit